

# Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

$$I_{FAV} = 65 \text{ A}$$

$$V_F = 1.11 \text{ V}$$

Phase leg

Part number

**MDMA65P1200TG**



Backside: isolated

 E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: TO-240AA

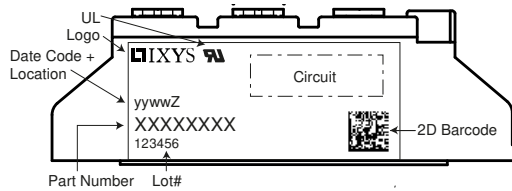
- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

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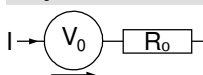
Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1300	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1200	V
$I_R$	reverse current	$V_R = 1200$ V		$T_{VJ} = 25^\circ\text{C}$		50	$\mu\text{A}$
		$V_R = 1200$ V		$T_{VJ} = 150^\circ\text{C}$		2	mA
$V_F$	forward voltage drop	$I_F = 65$ A		$T_{VJ} = 25^\circ\text{C}$		1.18	V
		$I_F = 130$ A				1.40	V
		$I_F = 65$ A		$T_{VJ} = 125^\circ\text{C}$		1.11	V
		$I_F = 130$ A				1.39	V
$I_{FAV}$	average forward current	$T_C = 100^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		65	A
		rectangular	d = 0.5				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.81	V
$r_F$	slope resistance					4.3	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.5	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.2		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		250	W
$I_{FSM}$	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		1.10	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		1.19	kA
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		935	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		1.01	kA
$I^2t$	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		6.05	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		5.89	kA <sup>2</sup> s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		4.37	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		4.25	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		37	pF

Package TO-240AA		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			200	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				76		g
$M_D$	mounting torque		2.5		4	Nm
$M_T$	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
$V_{ISOL}$	isolation voltage	t = 1 second			4800	V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		4000	V


**Part description**

M = Module  
 D = Diode  
 M = Standard Rectifier  
 A = (up to 1800V)  
 65 = Current Rating [A]  
 P = Phase leg  
 1200 = Reverse Voltage [V]  
 TG = TO-240AA

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA65P1200TG	MDMA65P1200TG	Box	36	515912

**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{VJ} = 150^{\circ}\text{C}$ 

**Rectifier**

$V_{0\max}$	threshold voltage	0.81	V
$R_{0\max}$	slope resistance *	3.1	mΩ



Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



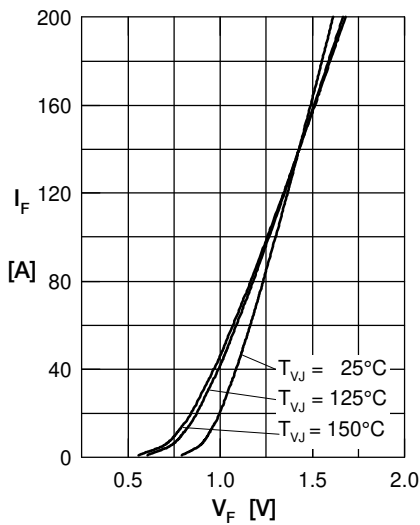
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

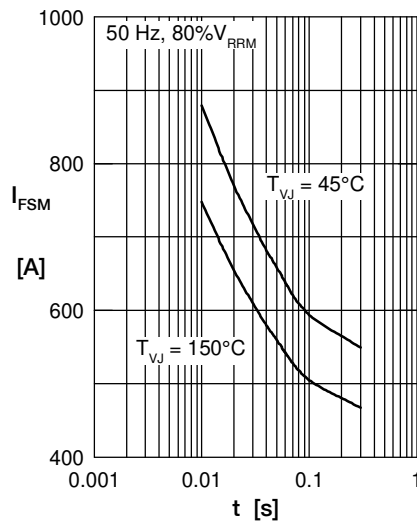


Fig. 2 Surge overload current vs. time per diode

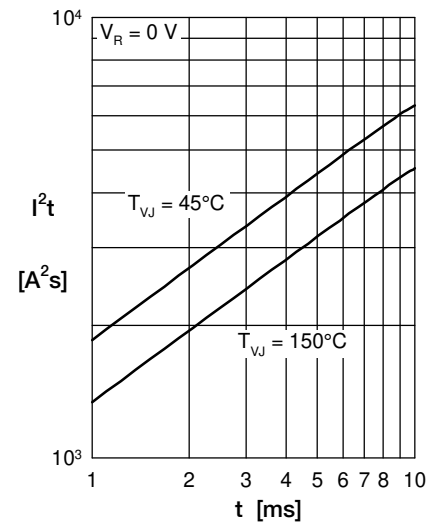
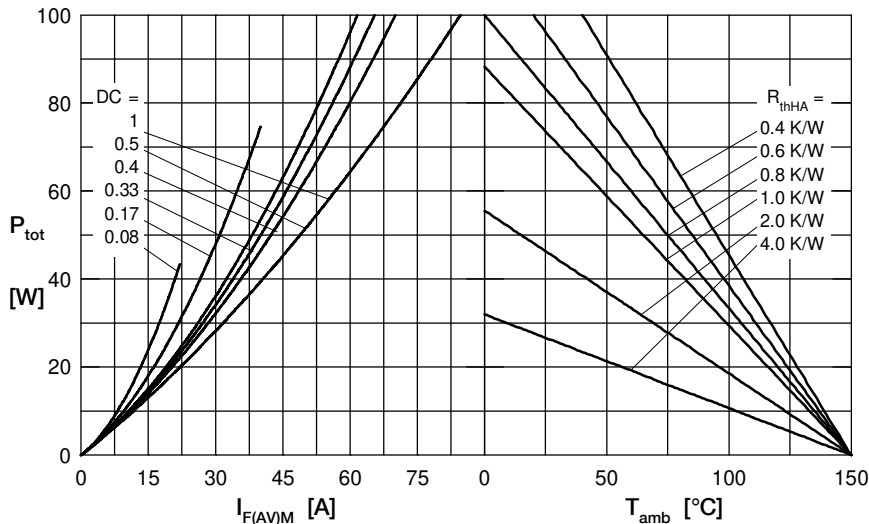

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

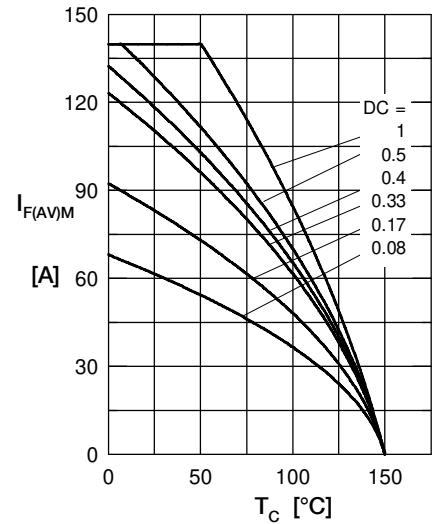


Fig. 5 Max. forward current vs. case temperature per diode

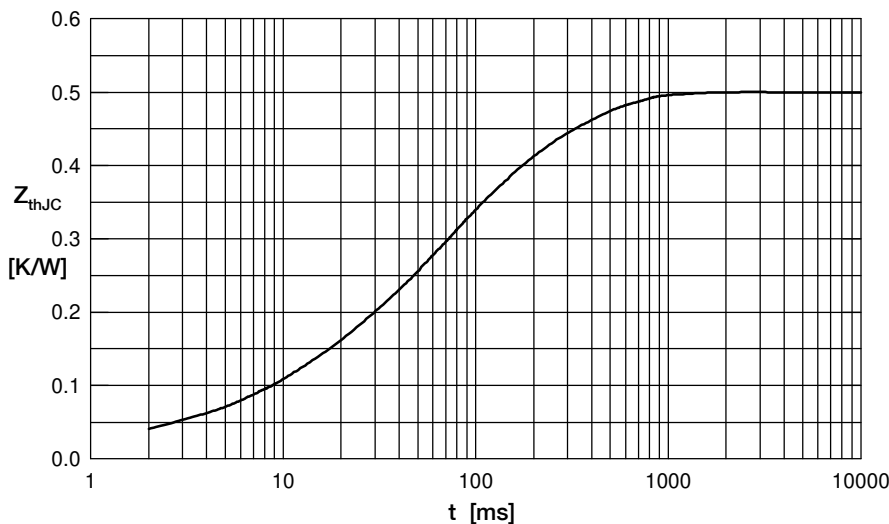


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.022	0.001
2	0.068	0.010
3	0.245	0.060
4	0.165	0.270